

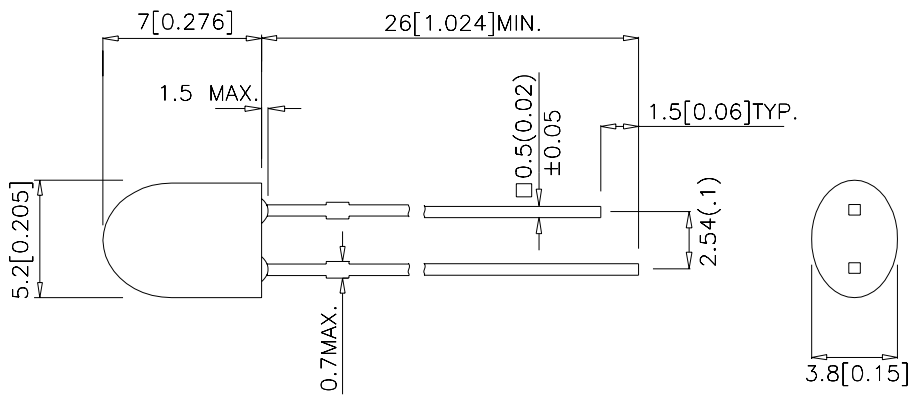
Features

- OUTSTANDING MATERIAL EFFICIENCY.
- RELIABLE AND RUGGED.
- IC COMPATIBLE/LOW CURRENT CAPABILITY.

Description

This devices are made with TS InGaAlP.

Package Dimensions



Notes:

1. All dimensions are in millimeters (inches).
2. Tolerance is ± 0.25 (0.01") unless otherwise noted.
3. Lead spacing is measured where the lead emerge package.
4. Specifications are subject to change without notice.

Selection Guide

Part No.	Dice	Lens Type	Iv (mcd) @ 20 mA		Viewing Angle
			Min.	Typ.	2θ1/2
W5603SYDL/H/SD	SUPER BRIGHT YELLOW (InGaAlP)	YELLOW SEMI DIFFUSED	380	750	100°(H) 50°(V)

Note:

1. θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 the optical centerline value.

Electrical / Optical Characteristics at T_A=25°C

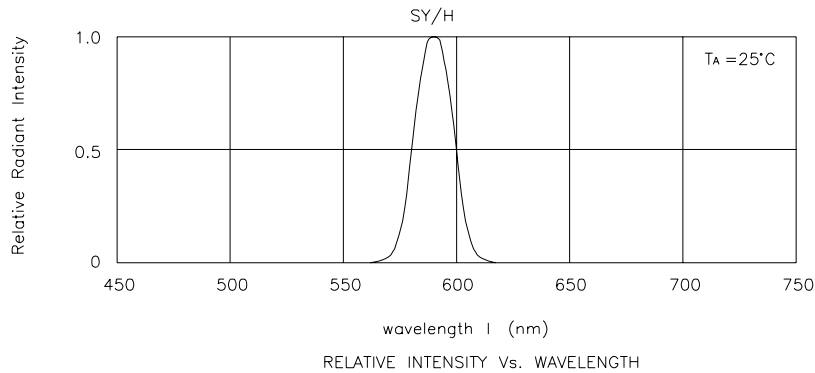
Symbol	Parameter	Device	Typ.	Max.	Units	Test Conditions
λ _{peak}	Peak Wavelength	Super Bright Yellow	590		nm	I _F =20mA
λ _D	Dominate Wavelength	Super Bright Yellow	589		nm	I _F =20mA
Δλ _{1/2}	Spectral Line Half-width	Super Bright Yellow	20		nm	I _F =20mA
C	Capacitance	Super Bright Yellow	45		pF	V _F =0V;f=1MHz
V _F	Forward Voltage	Super Bright Yellow	2.3	2.8	V	I _F =20mA
I _R	Reverse Current	Super Bright Yellow		10	uA	V _R = 5V

Absolute Maximum Ratings at T_A=25°C

Parameter	Super Bright Yellow	Units
Power dissipation	120	mW
DC Forward Current	30	mA
Peak Forward Current [1]	140	mA
Reverse Voltage	5	V
Operating/Storage Temperature	-40°C To +85°C	
Lead Solder Temperature [2]	260°C For 5 Seconds	

Notes:

- 1/10 Duty Cycle, 0.1ms Pulse Width.
- 2mm below package base.



Super Bright Yellow W5603SYDL/H/SD

